/ Descriptions

TO-262 N MOS N-CHANNEL MOSFET in a TO-262 Plastic Package..

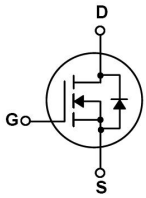
/ Features

Low gate charge, low crss, fast switching.

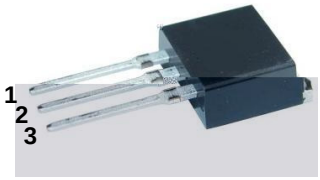
/ Applications

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

/ Equivalent Circuit



/ Pinning



PIN1 G PIN 2 D PIN 3 S

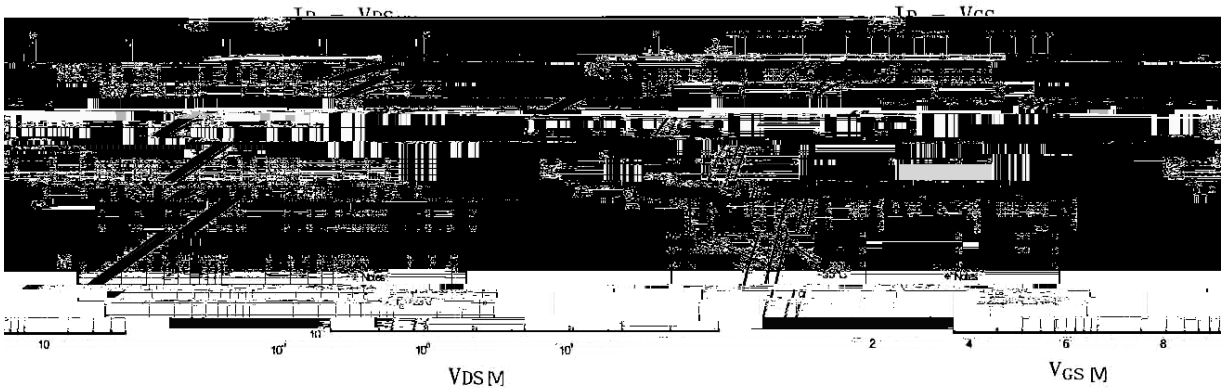
/ h_{FE} Classifications & Marking

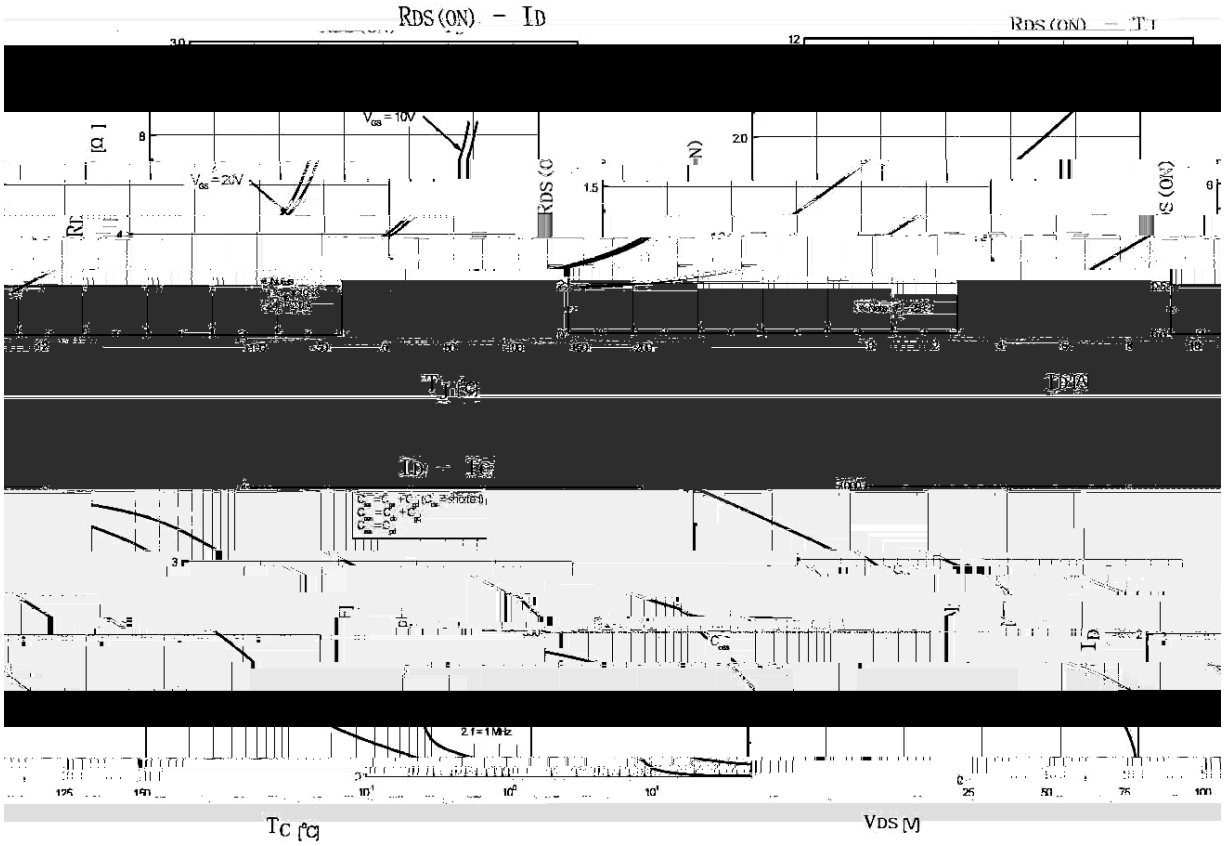
See Marking Instructions.

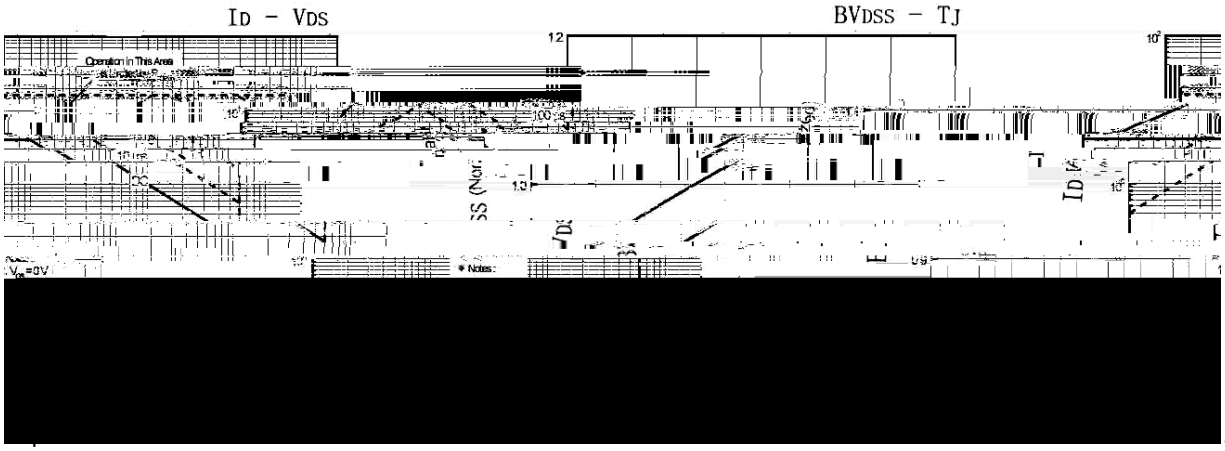
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	600	V
Drain Current	I_D(Tc=25)	4.0	A
Drain Current	I_D(Tc=100)	2.5	A
Drain Current - Pulsed	I_{DM}	16	A
Gate-Source Voltage	V_{GSS}	±30	V
Single Pulsed Avalanche Energy	E_{AS}	240	mJ
Repetitive Avalanche Energy	E_{AR}	10	mJ
Avalanche Current	I_{AR}	4.0	A
Power Dissipation	P_D(Tc=25)	100	W
Operating and Storage Temperature Range	T_J,T_{STG}	-55 to 150	

Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V	I_D=250μA	600			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=600V	V_{GS}=0V			10	μA
		V_{DS}=480V	T_C=125			100	μA
Gate-Body Leakage Current Forward	I_{GSS}	V_{GS}=±30V	V_{DS}=0V			±0.1	

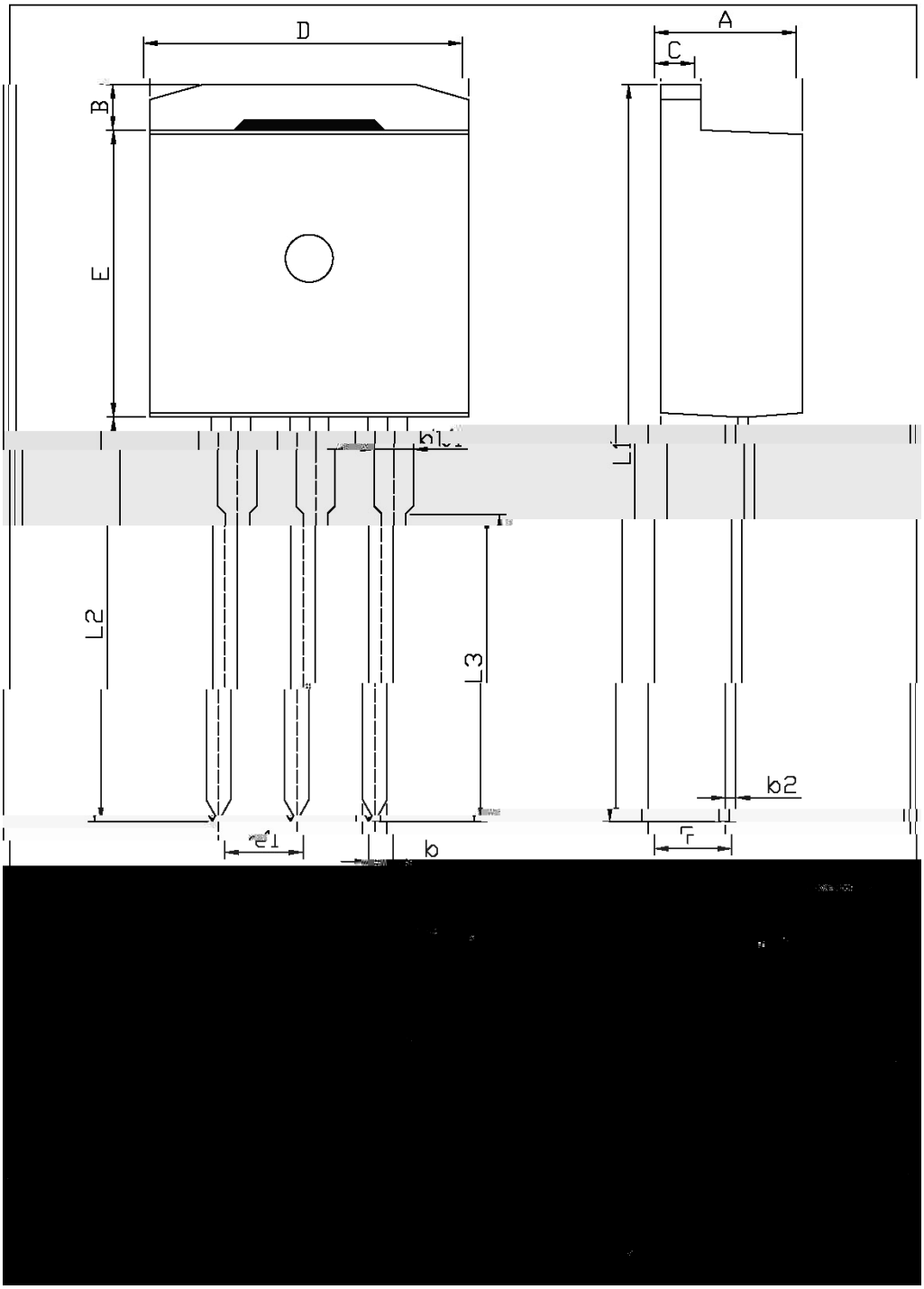
/ Electrical Characteristic Curve



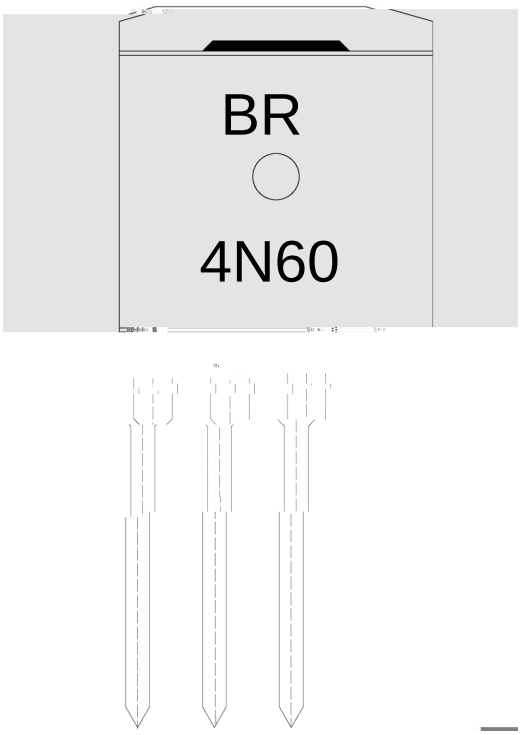




/ Package Dimensions



/ Marking Instructions



BR

4N60

Note:

BR:	Company Code
4N60:	Product Type.
****:	Lot No. Code, code change with Lot No.